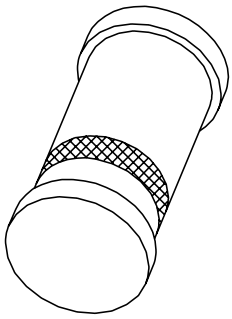
DATA SHEET



PMLL4150; PMLL4151; PMLL4153

High-speed diodes

Product data sheet
Supersedes data of April 1996

1996 Sep 18

High-speed diodes

PMLL4150; PMLL4151; PMLL4153

FEATURES

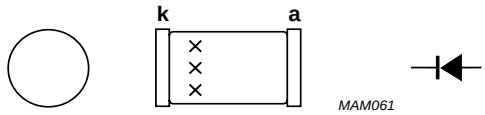
- Small hermetically sealed glass SMD package
- High switching speed: max. 4 ns
- General application
- Continuous reverse voltage: max. 50 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 600 mA and 450 mA respectively.

APPLICATIONS

- High-speed switching
- The PMLL4150 is primarily intended for general purpose use in computer and industrial applications.
- The PMLL4151 and PMLL4153 are intended for military and industrial applications.

DESCRIPTION

The PMLL4150, PMLL4151, PMLL4153 are high-speed switching diodes fabricated in planar technology, and encapsulated in small hermetically sealed glass SOD80C SMD packages.



Cathode indicated by black band.

Fig.1 Simplified outline (SOD80C) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage				
	PMLL4151		–	75	V
	PMLL4153		–	75	V
V_R	continuous reverse voltage		–	50	V
I_F	continuous forward current	see Fig.2; note 1			
	PMLL4150		–	300	mA
	PMLL4151		–	200	mA
	PMLL4153		–	200	mA
I_{FRM}	repetitive peak forward current				
	PMLL4150		–	600	mA
	PMLL4151		–	450	mA
	PMLL4153		–	450	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	–	4	A
		t = 1 ms	–	1	A
		t = 1 s	–	0.5	A
P_{tot}	total power dissipation	T_{amb} = 25 °C; note 1	–	500	mW
T_{stg}	storage temperature		−65	+200	°C
T_j	junction temperature		–	200	°C

Note

1. Device mounted on an FR4 printed-circuit board.

ELECTRICAL CHARACTERISTICS

T_j = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_F	forward voltage	see Fig.3			
	PMLL4150	I_F = 1 mA	540	620	mV
		I_F = 10 mA	660	740	mV
		I_F = 50 mA	760	860	mV
		I_F = 100 mA	820	920	mV
		I_F = 200 mA	870	1000	mV
	PMLL4151	I_F = 50 mA	–	1000	mV
	PMLL4153	I_F = 0.1 mA	490	550	mV
		I_F = 0.25 mA	530	590	mV
		I_F = 1 mA	590	670	mV
		I_F = 2 mA	620	700	mV
		I_F = 10 mA	700	810	mV
		I_F = 50 mA	740	880	mV
I_R	reverse current	V_R = 50 V; see Fig.5			
	PMLL4150		–	0.1	μA
	PMLL4151		–	0.05	μA
	PMLL4153		–	0.05	μA
I_R	reverse current	V_R = 50 V; T_j = 150 °C; see Fig.5			
	PMLL4150		–	100	μA
	PMLL4151		–	50	μA
	PMLL4153		–	50	μA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6			
	PMLL4150		–	2.5	pF
	PMLL4151		–	2	pF
	PMLL4153			2	pF

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
t_{rr}	reverse recovery time PMLL4150	when switched from I_F = 10 mA to I_R = 1 mA; R_L = 100 Ω; measured at I_R = 0.1 mA; see Fig.7	–	6	ns
		when switched from I_F = 10 mA to 200 mA to I_R = 10 mA to 200 mA; R_L = 100 Ω; measured at $I_R = 0.1 \times I_F$; see Fig.7	–	4	ns
		when switched from I_F = 200 mA to 400 mA to I_R = 200 mA to 400 mA; R_L = 100 Ω; measured at $I_R = 0.1 \times I_F$; see Fig.7	–	6	ns
t_{rr}	reverse recovery time PMLL4151	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	–	4	ns
		when switched from I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	–	2	ns
t_{rr}	reverse recovery time PMLL4153	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	–	4	ns
		when switched from I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	–	2	ns
t_{fr}	forward recovery time	when switched to I_F = 200 mA; t_r = 0.4 ns; measured at V_F = 1 V; see Fig.8	–	10	ns

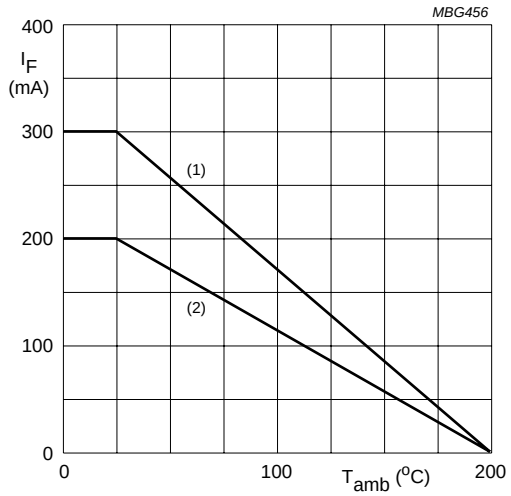
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point		300	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	350	K/W

Note

1. Device mounted on an FR4 printed-circuit board.

GRAPHICAL DATA

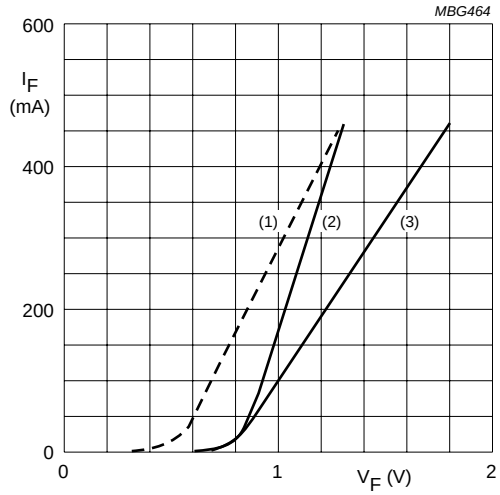


Device mounted on an FR4 printed-circuit board.

(1) PMLL4150.

(2) PMLL4151; PMLL4153.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.

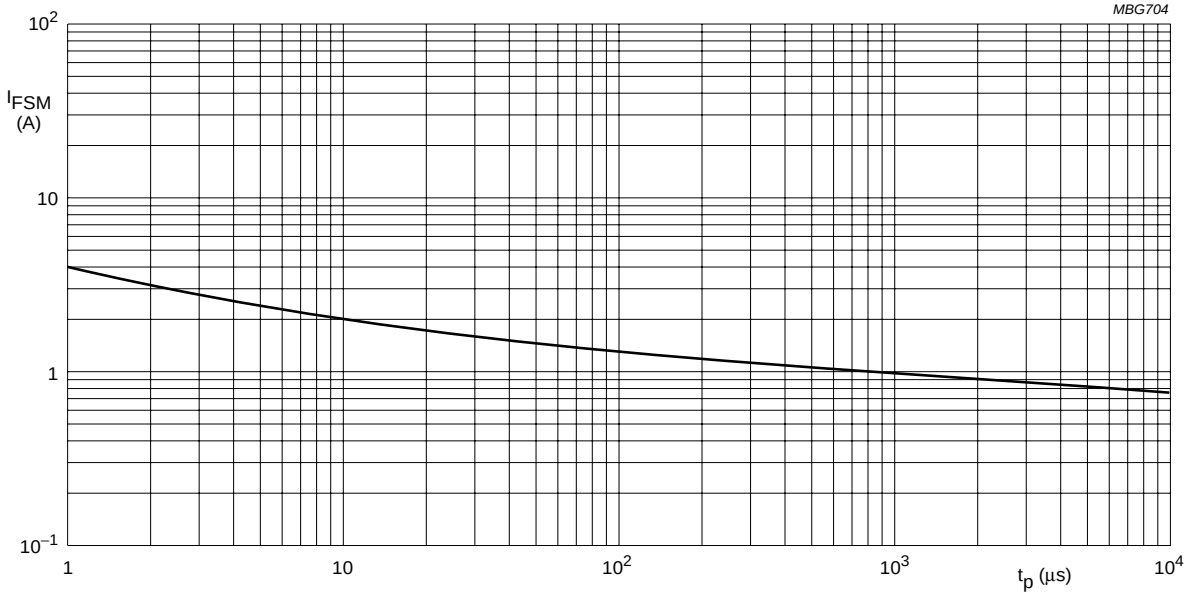


(1) T_j = 175 °C; typical values.

(2) T_j = 25 °C; typical values.

(3) T_j = 25 °C; maximum values.

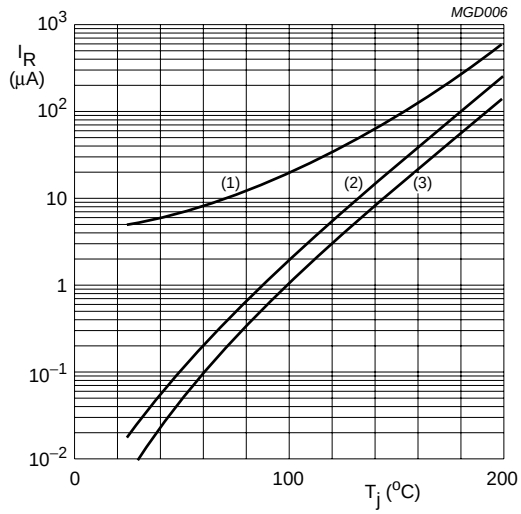
Fig.3 Forward current as a function of forward voltage.



Based on square wave currents.

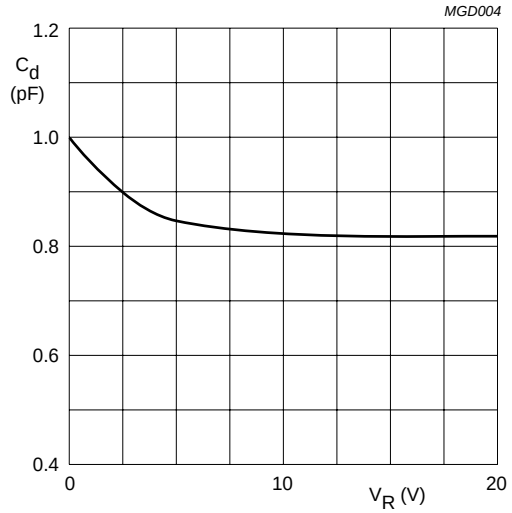
T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.



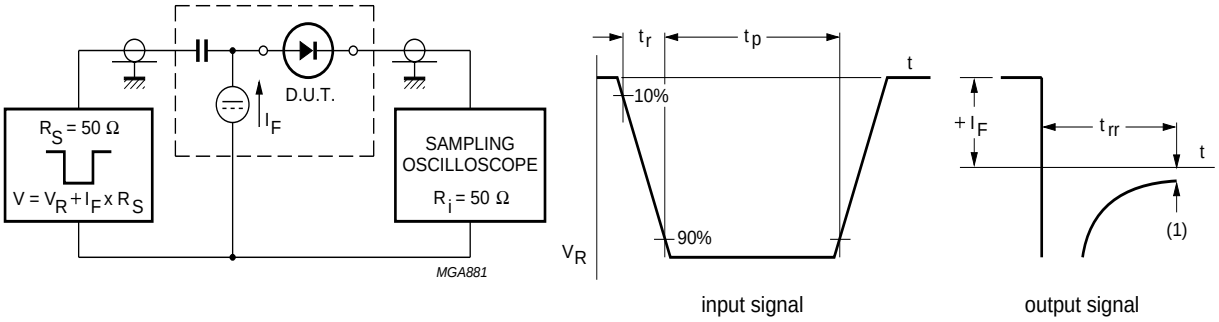
(1) V_R = 75 V; maximum values.
(2) V_R = 75 V; typical values.
(3) V_R = 20 V; typical values.

Fig.5 Reverse current as a function of junction temperature.



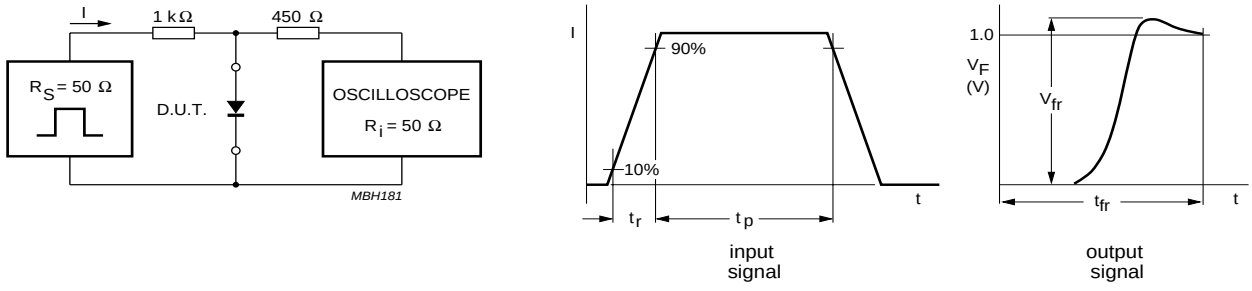
f = 1 MHz; T_j = 25 °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.



(1) The value of I_R is dependent on product type.

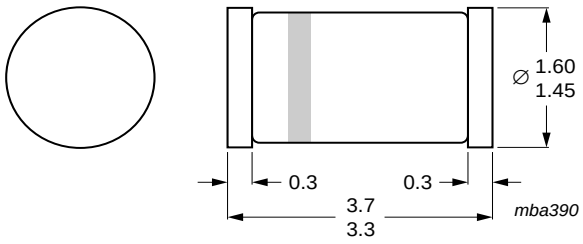
Fig.7 Reverse recovery voltage test circuit and waveforms.



Input signal: forward pulse rise time t_r = 0.4 ns; forward pulse duration t_p = 100 ns; duty factor δ = 0.01.

Fig.8 Forward recovery time test circuit and waveforms.

PACKAGE OUTLINE



Dimensions in mm.

Fig.9 SOD80C.

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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